

**APPLICATION**

- I/O ESD protection for mobile handsets, notebook, PDAs, etc.
- EMI filtering for data ports in cell phones, PDAs, notebook computers
- EMI filtering for LCD, camera and chip-to-chip data lines

**FEATURES**

- EMI/RFI filtering
- ESD Protection to IEC 61000-4-2 Level 4
- Low insertion loss
- Good attenuation of high frequency signals
- Low clamping voltage
- Low operating and leakage current
- Four elements in one package

**DESCRIPTION**

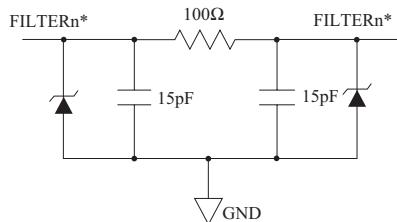
PF1010UDF8 is an EMI filter array with electrostatic discharge (ESD) protection, which integrates four pi filters (C-R-C). These parts include ESD protection diodes on every pin, providing a very high level of protection for sensitive electronic components that may be subjected to electrostatic discharge.

The PF1010UDF8 provides the recommended line termination while implementing a low pass filter to limit EMI levels and providing ESD protection which exceeds IEC 61000-4-2 level 4 standard. The UDFN package is a very effective PCB space occupation and a very thin package (0.4mm Pitch, 0.5mm height)

**MAXIMUM RATING (Ta=25 °C)**

| CHARACTERISTIC        | SYMBOL           | RATING  | UNIT |
|-----------------------|------------------|---------|------|
| DC Power Per Resistor | P <sub>R</sub>   | 100     | mW   |
| Power Dissipation     | *P <sub>D</sub>  | 400     |      |
| Junction Temperature  | T <sub>j</sub>   | 150     | °C   |
| Storage Temperature   | T <sub>stg</sub> | -55 150 | °C   |

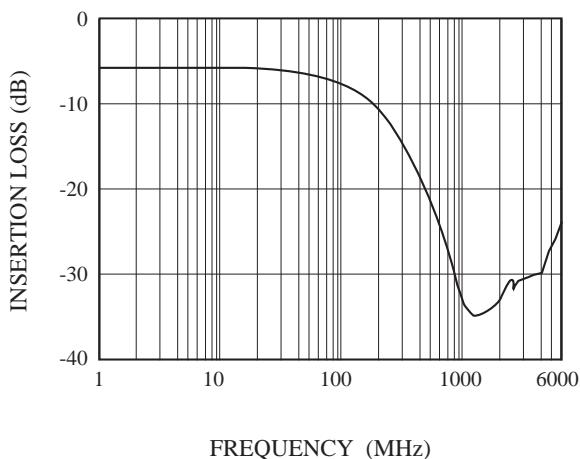
\* Total Package Power Dissipation

**EQUIVALENT CIRCUIT****ELECTRICAL CHARACTERISTICS (Ta=25 °C)**

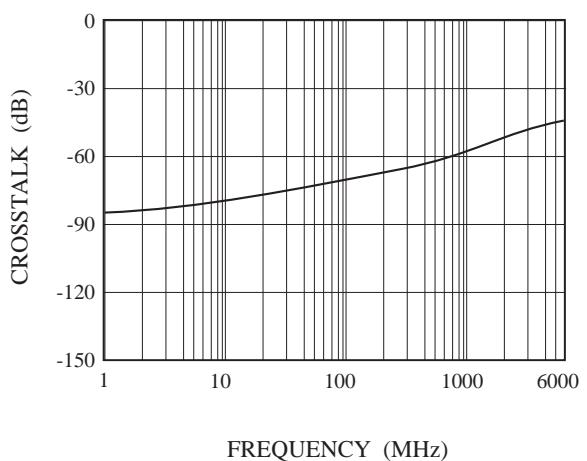
| CHARACTERISTIC            | SYMBOL             | TEST CONDITION  | MIN. | TYP. | MAX. | UNIT |
|---------------------------|--------------------|---|------|------|------|------|
| Reverse Stand-Off Voltage | V <sub>RWM</sub>   | -   | -    | -    | 5    | V    |
| Reverse Breakdown Voltage | V <sub>BR</sub>    | I <sub>f</sub> =1mA   | 6    | -    | -    | V    |
| Reverse Leakage Current   | I <sub>R</sub>     | V <sub>RWM</sub> =3.3V  | -    | -    | 1.0  | µA   |
| Cutoff Frequency          | f <sub>c-3dB</sub> | V <sub>Line</sub> =0V, Z <sub>SOURCE</sub> =50Ω, Z <sub>LOAD</sub> =50Ω | -    | 150  | -    | MHz  |
| Channel Resistance        | R <sub>LINE</sub>  | Between Input and Output  | 80   | 100  | 120  |      |
| Line Capacitance          | C <sub>LINE</sub>  | V <sub>Line</sub> =0V DC, 1MHz, Between I/O Pins and GND                | 24   | 30   | 36   | pF   |
|                           |                    | V <sub>Line</sub> =2.5V, 1MHz, Between I/O Pins and GND                 | 16   | 20   | 24   |      |

# PF1010UDF8

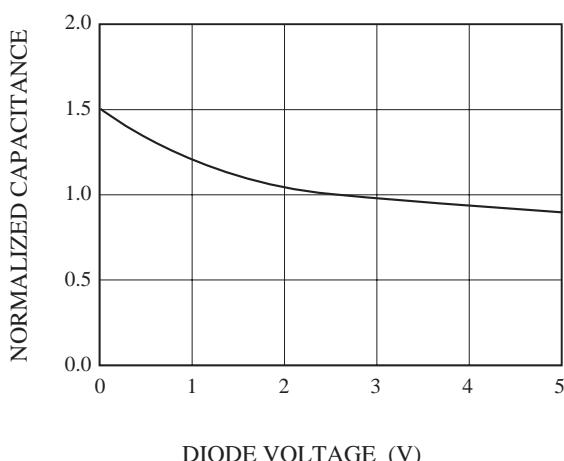
S<sub>21</sub> - FREQUENCY



ANALOG CROSSTALK



DIODE CAPACITANCE vs. INPUT VOLTAGE



R<sub>Line</sub> - TEMPERATURE

